

**MP 110 – MP 111
MP 115 – MP 112**

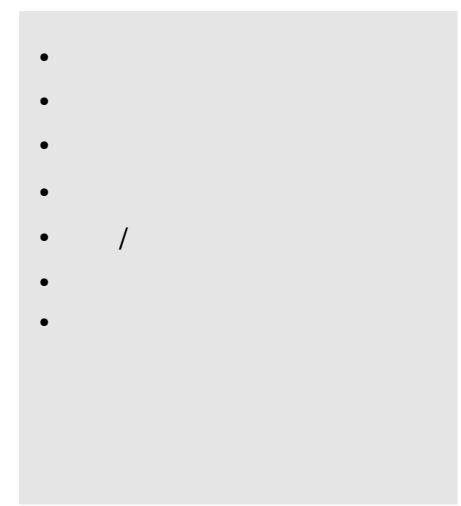
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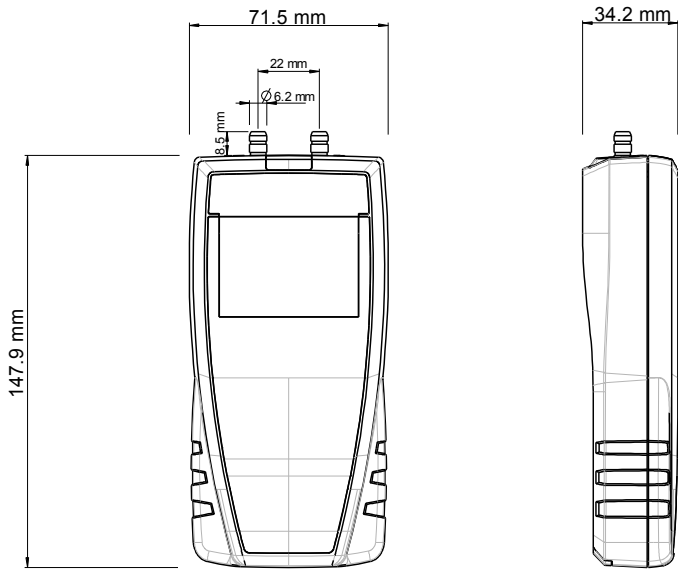
	MP 110 : 250 mbar / MP 111 : 700 mbar MP 115 : 1.4 bar / MP 112 : 3 bar
	MP 110 / 111 : Ø 6.2 mm MP 115 / 112 : Ø 4.6 mm
	4 , LCD, 50*36mm 2 () - 5 , 7 2 () - 5 , 16
	IP54 ABS
	5
	Directives CEM 2004/108/CE and NF EN 61010-1
	4 AAA LR03 1.5V
	18
	Neutral gas
	0 ~ 50
	-20 ~ 80
	0 ~ 120
	220g



MP110	Pa, mmH ₂ O inWg, daPa	- 1000 ~ 1000pa	±0.5% of reading ±2 Pa	1 Pa
MP111	Kpa, mmH ₂ O, inWg, mbar, mmHg, daPa	- 1000 ~ 1000 mmH ₂ O	±0.5% of reading ±2 mmH ₂ O	±200 mmH ₂ O : 0,1 mmH ₂ O : 1 mmH ₂ O
MP115	kPa, inWg, mbar, mmHg, PSI	-500 ~ 500mbar	±0.5% of reading ±0.5 mbar	0.1 mbar
MP112	kPa, inWg, mbar, mmHg, PSI, bar	-2000 ~ 2000 mbar	±0.5% of reading ±2 mt	1 mbar

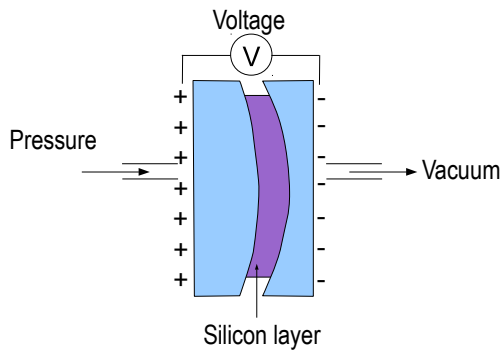
¹All the accuracies indicated in this technical datasheet were stated in laboratory conditions, and can be guaranteed for measurements carried out in the same conditions, or carried out with calibration compensation





Piezoresistive sensor

The pressure deforms the silicon layer. This layer deformation generates a voltage at its terminates. This voltage is proportional to the pressure applied.



- 2*1m 4*7mm
- 6*100mm
- (ST110)

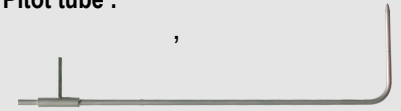


CQ 15 :



JTC ou JTY : T,Y
5*8mm

Pitot tube :



MT 51 : ABS



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